**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- · Trench MOSFET technology
- Side wettable flanks for optical solder inspection
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- AEC-Q101 qualified

## 3. Applications

- · Relay driver
- · High-speed line driver
- · High-side load switch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions  |     | Min | Тур | Max  | Unit |  |
|-------------------|----------------------------------|---|-----|-----|-----|------|------|--|
| $V_{DS}$          | drain-source voltage             | T <sub>j</sub> = 25 °C                            |     | -   | -   | -30  | V    |  |
| $V_{GS}$          | gate-source voltage              |   |     | -20 | -   | 20   | V    |  |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C | [1] | -   | -   | -6.1 | Α    |  |
| Static characte   | Static characteristics           |   |     |     |     |      |      |  |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS}$ = -10 V; $I_D$ = -6.1 A; $T_j$ = 25 °C   |     | -   | 24  | 29   | mΩ   |  |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

#### **Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline    | Graphic symbol |
|-----|--------|-------------|-----------------------|----------------|
| 1   | D      | drain       | 1 6                   | D              |
| 2   | D      | drain       |                       |                |
| 3   | G      | gate        | 2 5                   | G P            |
| 4   | S      | source      | 3 8 94                | S              |
| 5   | D      | drain       | Transparent top view  | 017aaa257      |
| 6   | D      | drain       | DFN2020MD-6 (SOT1220) |                |
| 7   | D      | drain       |                       |                |
| 8   | S      | source      |                       |                |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number | Package     |   |         |  |  |  |
|-------------|-------------|---|---------|--|--|--|
|             | Name        | Description   | Version |  |  |  |
| PMPB27EPA   | DFN2020MD-6 | DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals | SOT1220 |  |  |  |

# 7. Marking

### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMPB27EPA   | 4P           |

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# 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter   | Conditions  |     | Min | Max  | Unit |
|----------------------|---|---|-----|-----|------|------|
| V <sub>DS</sub>      | drain-source voltage                                | T <sub>j</sub> = 25 °C  |     | -   | -30  | V    |
| V <sub>GS</sub>      | gate-source voltage                                 |   |     | -20 | 20   | V    |
| I <sub>D</sub>       | drain current                                       | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 25 °C                   | [1] | -   | -6.1 | Α    |
|                      |   | V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C                  | [1] | -   | -3.9 | Α    |
| I <sub>DM</sub>      | peak drain current                                  | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$                 |     | -   | -25  | Α    |
| P <sub>tot</sub>     | total power dissipation                             | T <sub>amb</sub> = 25 °C  | [1] | -   | 1.7  | W    |
|                      |   | T <sub>sp</sub> = 25 °C   |     | -   | 12.5 | W    |
| T <sub>j</sub>       | junction temperature                                |   |     | -55 | 150  | °C   |
| T <sub>amb</sub>     | ambient temperature                                 |   |     | -55 | 150  | °C   |
| T <sub>stg</sub>     | storage temperature                                 |   |     | -65 | 150  | °C   |
| Source-drain         | n diode   |   |     |     |      |      |
| I <sub>S</sub>       | source current                                      | T <sub>amb</sub> = 25 °C  | [1] | -   | -1.9 | Α    |
| ESD maximu           | ım rating   |   |     |     |      |      |
| $V_{ESD}$            | electrostatic discharge voltage                     | НВМ   | [2] | -   | 1000 | V    |
| Avalanche ru         | uggedness   |   | '   | '   |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche<br>energy | $T_{j(init)}$ = 25 °C; $I_D$ = -1.7 A; DUT in avalanche (unclamped) |     | -   | 26.8 | mJ   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Measured between all pins.

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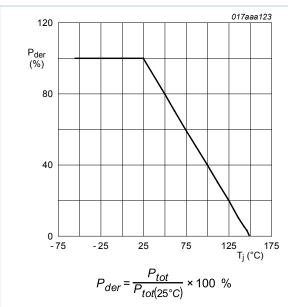


Fig. 1. Normalized total power dissipation as a function of junction temperature

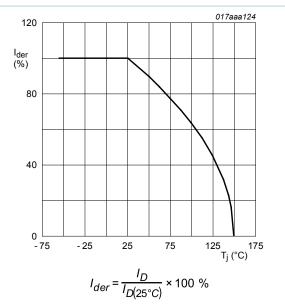
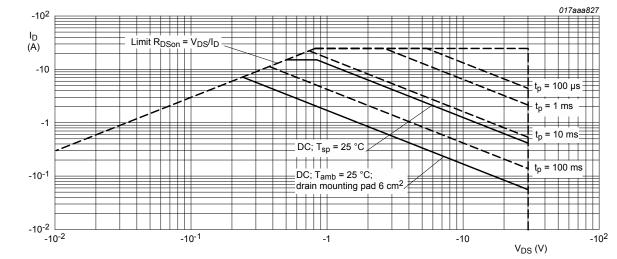


Fig. 2. Normalized continuous drain current as a function of junction temperature



I<sub>DM</sub> = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter   | Conditions  |     | Min | Тур | Max | Unit |
|-----------------------|---|-------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient | in free air | [1] | -   | 235 | 270 | K/W  |
|                       |   |             | [2] | -   | 67  | 74  | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point  |             |     | -   | 5   | 10  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

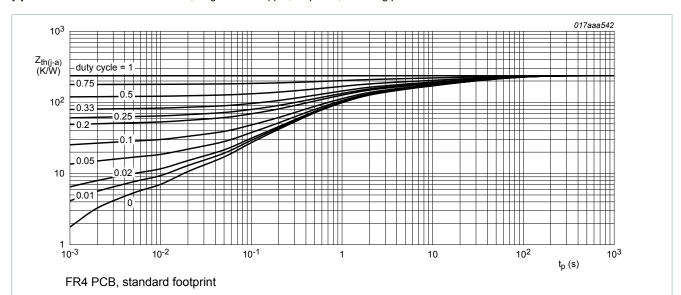


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

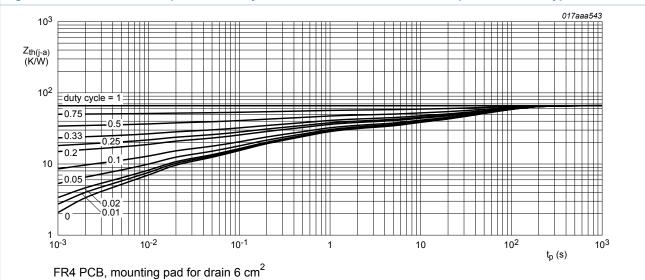


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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## 10. Characteristics

#### Table 7. Characteristics

| Symbol                           | Parameter                         | Conditions   | Min | Тур  | Max  | Unit |
|----------------------------------|-----------------------------------|--|-----|------|------|------|
| Static chara                     | acteristics                       |  |     | '    | -    | ,    |
| V <sub>(BR)DSS</sub>             | drain-source<br>breakdown voltage | $I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$             | -30 | -    | -    | V    |
| $V_{GSth}$                       | gate-source threshold voltage     | $I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$                   | -1  | -1.5 | -2.5 | V    |
| I <sub>DSS</sub>                 | drain leakage current             | $V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$        | -   | -    | -1   | μΑ   |
| I <sub>GSS</sub> gate leakage co | gate leakage current              | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$  | -   | -    | -100 | nA   |
|                                  |                                   | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C      | -   | -    | 100  | nA   |
| R <sub>DSon</sub>                | drain-source on-state             | $V_{GS}$ = -10 V; $I_D$ = -6.1 A; $T_j$ = 25 °C                            | -   | 24   | 29   | mΩ   |
| resistance                       | resistance                        | V <sub>GS</sub> = -10 V; I <sub>D</sub> = -6.1 A; T <sub>j</sub> = 150 °C  | -   | 37   | 45   | mΩ   |
|                                  |                                   | $V_{GS} = -4.5 \text{ V}; I_D = -5 \text{ A}; T_j = 25 ^{\circ}\text{C}$   | -   | 32   | 43   | mΩ   |
| g <sub>fs</sub>                  | forward transconductance          | $V_{DS}$ = -10 V; $I_D$ = -6.1 A; $T_j$ = 25 °C                            | -   | 26   | -    | S    |
| R <sub>G</sub>                   | gate resistance                   | f = 1 MHz  | -   | 5.4  | -    | Ω    |
| Dynamic ch                       | naracteristics                    |  |     |      | 1    |      |
| Q <sub>G(tot)</sub>              | total gate charge                 | $V_{DS}$ = -15 V; $I_{D}$ = -6.1 A; $V_{GS}$ = -10 V;                      | -   | 30   | 45   | nC   |
| Q <sub>GS</sub>                  | gate-source charge                | T <sub>j</sub> = 25 °C   | -   | 4.8  | -    | nC   |
| $Q_{GD}$                         | gate-drain charge                 |  | -   | 6.3  | -    | nC   |
| C <sub>iss</sub>                 | input capacitance                 | V <sub>DS</sub> = -15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                 | -   | 1570 | -    | pF   |
| C <sub>oss</sub>                 | output capacitance                | T <sub>j</sub> = 25 °C   | -   | 170  | -    | pF   |
| C <sub>rss</sub>                 | reverse transfer capacitance      |  | -   | 150  | -    | pF   |
| t <sub>d(on)</sub>               | turn-on delay time                | V <sub>DS</sub> = -15 V; I <sub>D</sub> = -6.1 A; V <sub>GS</sub> = -10 V; | -   | 10   | -    | ns   |
| t <sub>r</sub>                   | rise time                         | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$                                       | -   | 31   | -    | ns   |
| t <sub>d(off)</sub>              | turn-off delay time               |  | -   | 28   | -    | ns   |
| t <sub>f</sub>                   | fall time                         |  | -   | 19   | -    | ns   |
| Source-dra                       | in diode                          |  | 1   |      |      |      |
| V <sub>SD</sub>                  | source-drain voltage              | $I_S = -1.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$    | -   | -0.8 | -1.2 | V    |
| t <sub>rr</sub>                  | reverse recovery time             | $I_S = -1.9 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$               | -   | 14   | -    | ns   |
| Q <sub>r</sub>                   | recovered charge                  | $V_{GS} = 0 \text{ V}; V_{DS} = -15 \text{ V}; T_j = 25 \text{ °C}$        | _   | 6    | _    | nC   |

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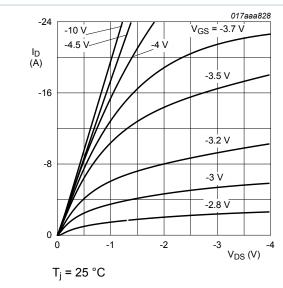


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

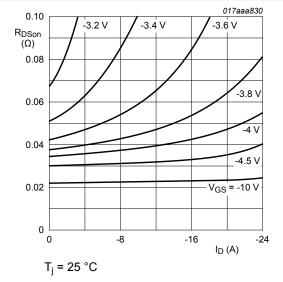


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

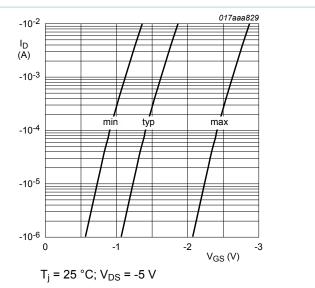


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

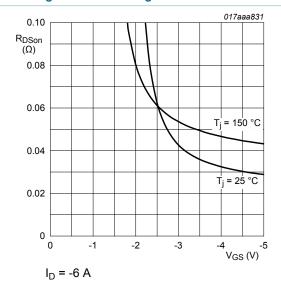


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 30 V, P-channel Trench MOSFET

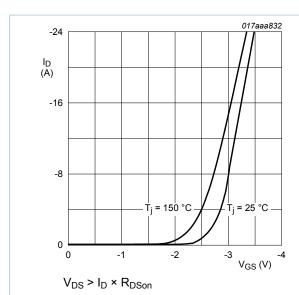


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

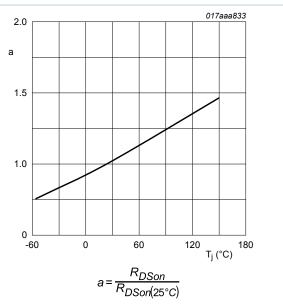


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

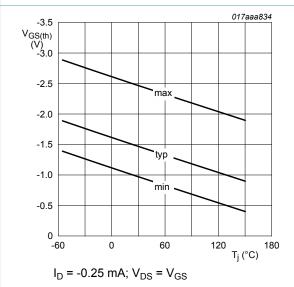


Fig. 12. Gate-source threshold voltage as a function of junction temperature

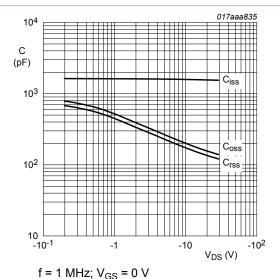


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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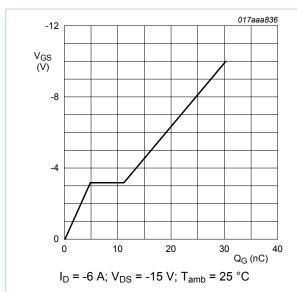


Fig. 14. Gate-source voltage as a function of gate charge; typical values

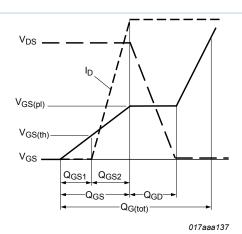


Fig. 15. Gate charge waveform definitions

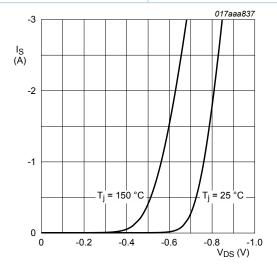
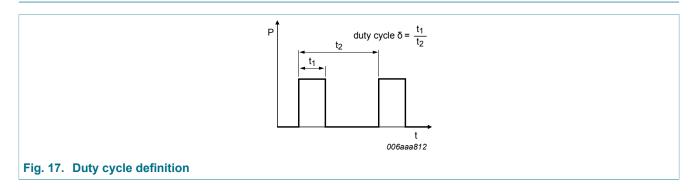


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$ 

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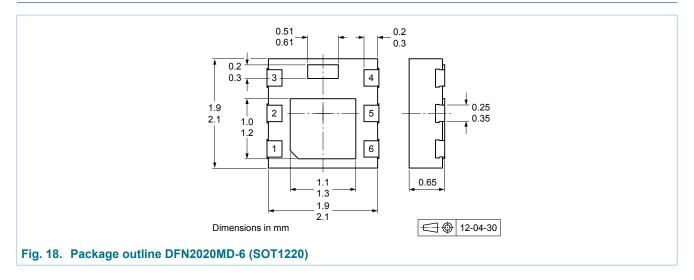
### 11. Test information



### **Quality information**

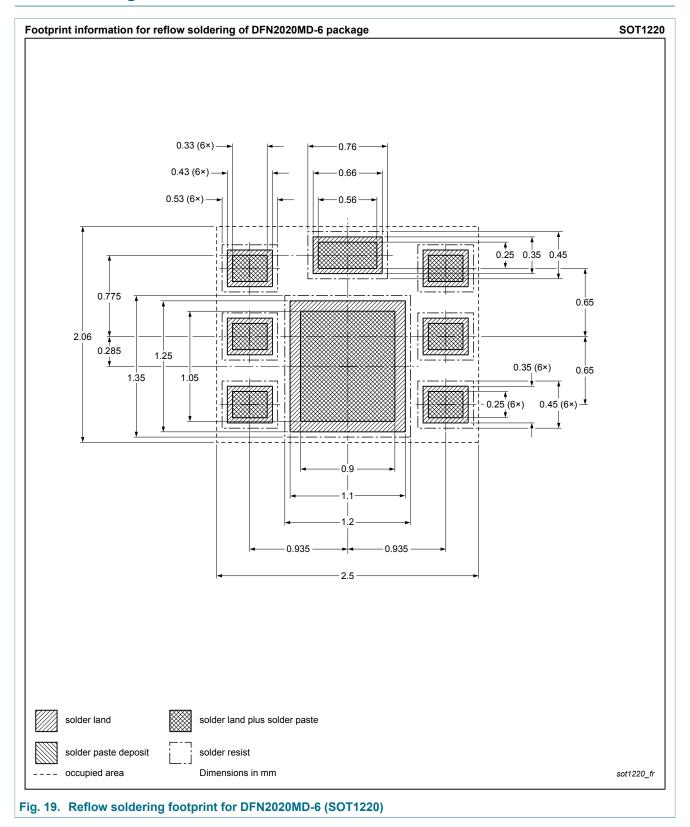
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



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## 13. Soldering



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# 14. Revision history

### Table 8. Revision history

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMPB27EPA v.1 | 20180327     | Product data sheet | -             | -          |

#### 30 V, P-channel Trench MOSFET

## 15. Legal information

#### **Data sheet status**

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 27 March 2018

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